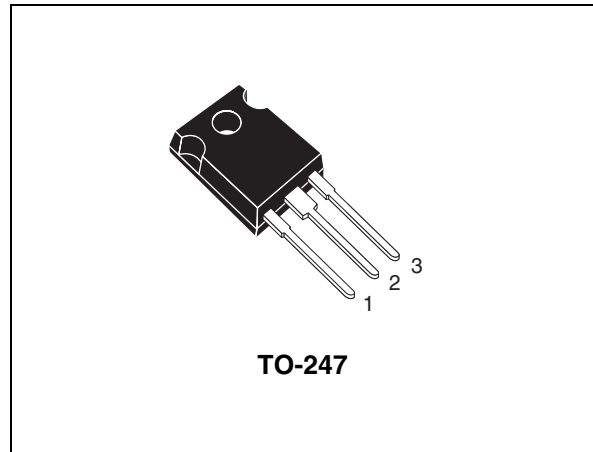


Features

- Maximum junction temperature : $T_J = 175\text{ }^\circ\text{C}$
- High speed switching
- Minimized tail current
- Low saturation voltage: $V_{CE(sat)} = 2.1\text{ V (typ.)}$
@ $I_C = 40\text{ A}$
- Safe paralleling
- 10 μs short-circuit withstand time at $T_J = 150\text{ }^\circ\text{C}$
- Ultrafast free-wheeling diode co-packaged
- Low thermal resistance
- Lead free package



Applications

- Uninterruptible power supply
- Welding machines
- Photovoltaic inverters
- Power factor correction
- High switching frequency converters

Description

This device is an IGBT developed using an advanced proprietary trench gate and field stop structure. The device is part of the "H" series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of high switching frequency converters. Moreover, a slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Figure 1. Internal schematic diagram

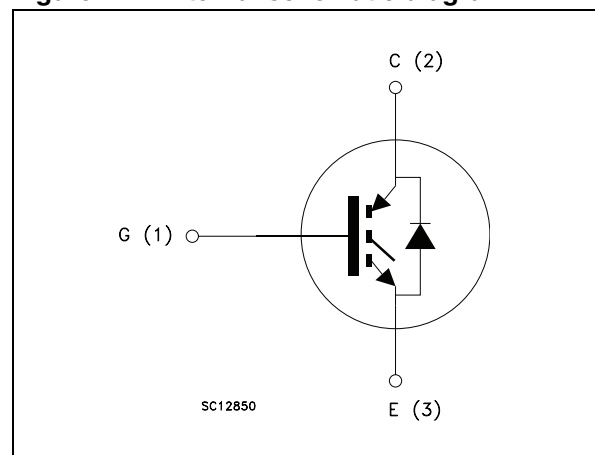


Table 1. Device summary

Order code	Marking	Package	Packaging
STGW40H120DF2	GW40H120DF2	TO-247	Tube

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)	1200	V
I_C	Continuous collector current at $T_C = 25\text{ °C}$	80	A
I_C	Continuous collector current at $T_C = 100\text{ °C}$	40	A
$I_{CP}^{(1)}$	Pulsed collector current	160	A
V_{GE}	Gate-emitter voltage	± 20	V
I_F	Continuous collector current at $T_C = 25\text{ °C}$	50	A
	Continuous collector current at $T_C = 100\text{ °C}$	25	A
$I_{FP}^{(1)}$	Pulsed forward current	100	A
t_{SC}	Short-circuit withstand time at $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $T_J = 150\text{ °C}$	10	μs
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	TBD	W
T_J	Operating junction temperature	- 55 to 175	$^{\circ}\text{C}$
T_{STG}	Storage temperature range		

1. Pulse width limited by maximum junction temperature and turn-off within RBSOA

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case IGBT	TBD	$^{\circ}\text{C}/\text{W}$
R_{thJC}	Thermal resistance junction-case diode	TBD	$^{\circ}\text{C}/\text{W}$
R_{thJA}	Thermal resistance junction-ambient	TBD	$^{\circ}\text{C}/\text{W}$

2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1\text{ mA}$	1200			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$ $V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$, $T_J = 175\text{ °C}$		2.1 2.4		V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$		5		V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 1200\text{ V}$ $V_{CE} = 1200\text{ V}$, $T_J = 125\text{ °C}$			250 TBD	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			250	nA

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$		TBD		pF
C_{oes}	Output capacitance		-	TBD	-	pF
C_{res}	Reverse transfer capacitance				TBD	pF
Q_g	Total gate charge	$V_{CE} = 600\text{ V}$, $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$		TBD		nC
Q_{ge}	Gate-emitter charge		-	TBD	-	nC
Q_{gc}	Gate-collector charge				TBD	nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 600\text{ V}$, $I_C = 40\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 2)	-	TBD TBD TBD	-	ns ns A/ μ s
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 600\text{ V}$, $I_C = 40\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$ (see Figure 2)	-	TBD TBD TBD	-	ns ns A/ μ s
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 600\text{ V}$, $I_C = 40\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 2)	-	TBD TBD TBD	-	ns ns ns
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 600\text{ V}$, $I_C = 40\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$ (see Figure 2)	-	TBD TBD TBD	-	ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$ $E_{off}^{(2)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 600\text{ V}$, $I_C = 40\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 2)	-	TBD 1.5 TBD	-	mJ mJ mJ
$E_{on}^{(1)}$ $E_{off}^{(2)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 600\text{ V}$, $I_C = 40\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$ (see Figure 2)	-	TBD 2.2 TBD	-	mJ mJ mJ

1. Energy losses include reverse recovery of the diode
2. Turn-off losses include also the tail of the collector current

Table 8. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	$I_F = 40\text{ A}$ $I_F = 40\text{ A}$, $T_J = 175\text{ }^\circ\text{C}$	-	TBD	TBD	V V
t_{rr} Q_{rr} I_{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_F = 40\text{ A}$, $V_R = 45\text{ V}$, $R_G = 10\ \Omega$ (see Figure 5)	-	TBD TBD TBD	-	ns nC A
t_{rr} Q_{rr} I_{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_F = 40\text{ A}$, $V_R = 45\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$, $R_G = 10\ \Omega$ (see Figure 5)	-	TBD TBD TBD	-	ns nC A

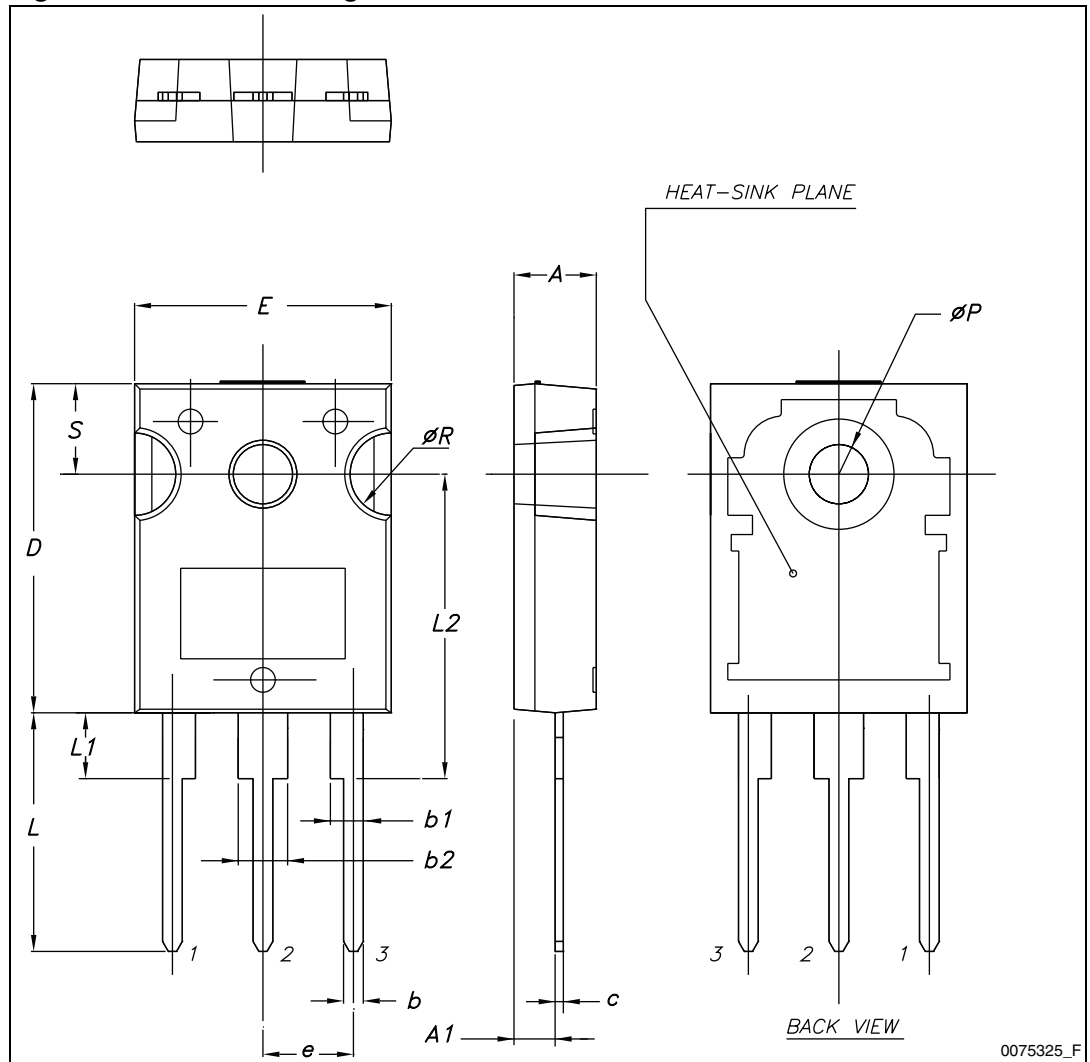
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 9. TO-247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S		5.50	

Figure 6. TO-247 drawing



5 Revision history

Table 10. Document revision history

Date	Revision	Changes
03-Oct-2012	1	Initial release.

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